

20A Low Barrier Diode

## ■ Features

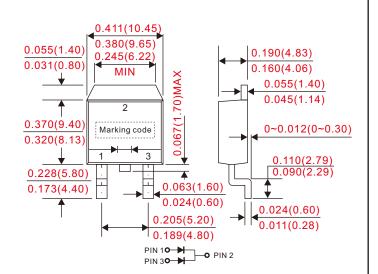
- · Low forward voltage drop.
- Excellent high temperature stability.
- Fast switching capability.
- Suffix "G" indicates Halogen-free part, ex.CSB20S45CTG-A.
- Lead-free parts meet environmental standards of MIL-STD-19500 /228

## ■ Mechanical data

- Epoxy: UL94-V0 rated flame retardant.
- Case: JEDEC TO-220AB molded plastic body over passivated chip.
- Lead : Axial leads, solderable per MIL-STD-202, Method 208 guranteed.
- Polarity: Color band denotes cathode end.
- Mounting Position : Any.
- Weight: Approximated 2.25 gram.

## Outline

D<sup>2</sup>PAK(TO-263)



## ■ Maximum ratings and electrical characteristics

Rating at  $25^{\circ}$ C ambient temperature unless otherwise specified. Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Parameter	Conditions	Symbol	CSB20S45CT-A		
Marking code			CSB20S45CT	UNIT	
Peak repetitive reverse voltage		V <sub>RRM</sub>			
Working peak reverse voltage		V <sub>RWM</sub>	45	V	
DC blocking voltage		V <sub>RM</sub>			
Forward rectified current (total device)		Io	20	Α	
Forward surge current (per diode)	8.3ms single half sine-wave superimposed on rate load (JEDEC method)	I <sub>FSM</sub>	200	А	
Peak repetitive reverse surge current (per diode)	2us - 1kHz	I <sub>RRM</sub>	3	А	
Thermal resistance(1) (per diode)	Junction to ambient	R <sub>eJC</sub>	30	°C/W	
Operating and Storage temperature		T <sub>J</sub> , T <sub>STG</sub>	-65 ~ +150	°C	

Parameter	Conditions	Symbol	MIN.	TYP.	MAX.	UNIT
Forward voltage drop (per diode)	$I_F = 10A, T_J = 25^{\circ}C$	V <sub>F</sub>			470	mV
	$I_{F} = 10A, T_{J} = 125^{\circ}C$				440	
	$I_F = 20A, T_J = 25^{\circ}C$				600	
Reverse current (per diode)	$V_R = V_{RRM} T_J = 25^{\circ}C$	- I <sub>R</sub>			0.5	mA
	$V_R = V_{RRM} T_J = 125^{\circ}C$				100	

Note: 1.Thermal resistance from junction to case per leg, with heatsink size(1.35" x 0.95" x 0.18") Al-plate.

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■ Rating and characteristic curves

Fig.1 - Forward Current Derating Curve (per diode)

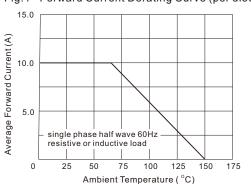


Fig. 2 - Instantaneous Forward Characteristics (per diode)

100

T<sub>A</sub>=150°C

T<sub>A</sub>=125°C

T<sub>A</sub>=75°C

100

0.01

0.01

0.01

0.02

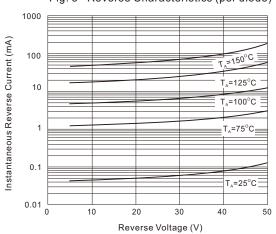
0.3

0.4

0.5

Instantaneous Forward Voltage (Volts)

Fig. 3 - Reverse Characteristics (per diode)



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